

**1.8W PNP GENERAL PURPOSE
SMALL SIGNAL TRANSISTORS**

T-3M-17

2N2906
2N2907

These transistors are silicon planar epitaxial pnp devices conforming to JEDEC TO-18, BS SO-132A and IEC C7/B11 outlines.

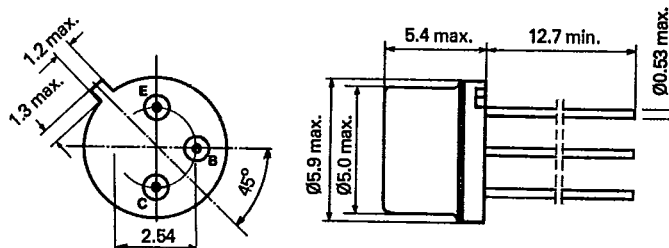
They are designed for high speed saturated switching and general purpose applications.

QUICK REFERENCE DATA

	2N2906	2N2907
$V_{CB0max.}$	60V	
$V_{CE0max.}$	40V	
$V_{CE(sat)max.}$ at $I_C = 500mA$, $I_B = 50mA$ and $T_{amb} = 25^\circ C$	1.6V	
$I_{Cmax.}$	600mA	
$h_{FEmin.}$ at $V_{CE} = 10V$, $I_C = 150mA$ and $T_{amb} = 25^\circ C$	40	100
$P_{totmax.}$ at $T_{amb} = 25^\circ C$	0.4W	

Outline and Dimensions

JEDEC TO-18
BS SO-132A
IEC C7/B11



All dimensions in millimetres
For detail dimensions see Page 4

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In the interest of improved product design, changes
to this specification may be made at any time.



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RATINGS 81C 00120 D

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The ratings quoted are limiting values of operating and environmental conditions and are in accordance with the absolute maximum rating system defined in BS 3494 (Part 1) and IEC Publication 134.

Voltage Ratings

V _{CBO}	Collector-base voltage at $I_E = 0$	60V
V _{CEO}	Collector-emitter voltage at $I_B = 0$	40V
V _{EBO}	Emitter-base voltage at $I_C = 0$	5V

Current Rating

I _C	Collector current (continuous)	600mA
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Power Ratings

P _{tot}	Total power dissipation	
	T _{amb} = 25°C	0.4W
	T _{case} = 25°C	1.8W

Thermal Ratings

T _j	Operating junction temperature range	-65°C to +200°C
T _{stg}	Storage temperature range	-65°C to +200°C

CHARACTERISTICS**Electrical Characteristics**

	Min.	Typ.	Max.
I _{CBO}	Collector-base cut-off current V _{CB} = 50V, I _E = 0 and T _{amb} = 25°C V _{CB} = 50V, I _E = 0 and T _{amb} = 150°C		
			20nA 20μA
I _{CEX}	Collector-emitter cut-off current at V _{CE} = 30V, V _{BE} = 0.5V and T _{amb} = 25°C		
			50nA
I _{BEX}	Base-emitter cut-off current at V _{BE} = 0.5V, V _{CE} = 30V and T _{amb} = 25°C		
			50nA
V _{CBO}	Collector-base voltage at I _C = 10μA, I _E = 0 and T _{amb} = 25°C		
	60V		
V _{CEO(sus)}	*Collector-emitter sustaining voltage at I _C = 10mA, I _B = 0 and T _{amb} = 25°C		
	40V		
V _{EBO}	Emitter-base voltage at I _C = 0, I _E = 10μA and T _{amb} = 25°C		
	5V		
V _{BE(sat)}	*Base-emitter saturation voltage I _C = 150mA, I _B = 15mA and T _{amb} = 25°C I _C = 500mA, I _B = 50mA and T _{amb} = 25°C		
			1.3V 2.6V
V _{CE(sat)}	*Collector-emitter saturation voltage I _C = 150mA, I _B = 15mA and T _{amb} = 25°C I _C = 500mA, I _B = 50mA and T _{amb} = 25°C		
			0.4V 1.6V

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2N2907

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Electrical Characteristics (continued)

		Min.	Typ.	Max.
h_{FE}	Static value of common emitter forward current transfer ratio $V_{CE} = 10V, I_C = 0.1mA$ and $T_{amb} = 25^\circ C$			
	2N2906	20		
	2N2907	35		
	$V_{CE} = 10V, I_C = 1.0mA$ and $T_{amb} = 25^\circ C$			
	2N2906	25		
	2N2907	50		
	$V_{CE} = 10V, I_C = 10mA$ and $T_{amb} = 25^\circ C$			
	2N2906	35		
	2N2907	75		
f_T	Transition frequency at $V_{CE} = 20V, I_C = 50mA, f = 100MHz$ and $T_{amb} = 25^\circ C$			
	2N2906	40		120
	2N2907	100		300
	$V_{CE} = 10V, I_C = 500mA^*$ and $T_{amb} = 25^\circ C$			
C_{EBO}	Emitter-base capacitance at $V_{EB} = 2V, I_C = 0, f = 100 kHz$ and $T_{amb} = 25^\circ C$			
				30pF
C_{CBO}	Collector-base capacitance at $V_{CB} = 10V, I_E = 0, f = 100 kHz$ and $T_{amb} = 25^\circ C$			
				8pF

*Pulsed; $t_p = 300 \mu s$; duty cycle 1%
Switching Times
 $(I_C = 150mA, I_{B1} = -I_{B2} = 15mA, V_{CC} = 30V (t_d \text{ and } t_r)$
 or $6V (t_s \text{ and } t_f)$ and $T_{amb} = 25^\circ C$

		Min.	Typ.	Max.
t_d	Delay time			10ns
t_r	Rise time			40ns
t_s	Storage time			80ns
t_f	Fall time			30ns

Thermal Characteristics

		Min.	Typ.	Max.
$R_{th(j-case)}$	Thermal resistance (junction to case)			97.3 deg C/W
$R_{th(j-amb)}$	Thermal resistance (junction to ambient)			437.5 deg C/W

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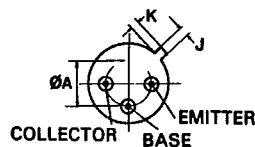
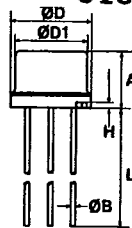
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MECHANICAL DETAILS

Outline and Dimensions

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Ref.	Millimetres		Inches		Notes
	Min.	Max.	Min.	Max.	
A	4.32	5.33	0.170	0.210	
ØA	2.54 nom.		0.100 nom.		
ØB	0.41	0.53	0.016	0.021	
ØD	5.31	5.84	0.209	0.230	
ØD1	4.52	4.95	0.178	0.195	
H	0.13	0.76	0.005	0.030	
J	0.92	1.16	0.036	0.046	
K	0.71	1.21	0.028	0.048	
L	12.7	—	0.500	—	

Notes

- The transistors conform to BS SO-132A, IEC C7/B11 and JEDEC TO-18 outlines.
- The millimetre dimensions are derived from the inch dimensions.

Weight 0.3 gramme.

INSTALLATION NOTES

The emitter, base and collector leads are identified on the transistor outline. Note the collector is connected also to the case.

The leads must not be bent within 0.06in (1.5mm) of the seals.

When soldering, a thermal shunt should be used to protect the transistor.

The transistor leads may be dip-soldered at at temperature of 240°C for 10 seconds up to a point 0.04in (1mm) from the seals.

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